

L Number	Hits	Search Text	DB	Time stamp
11	26	(plasma or "dry etching") and "negative ion" and bias and (pulse or pulsed or pulsing) and (RF or "radio frequency") and (chlorine or "Cl.sub.2")	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:01
12	1280	(plasma or "dry etching") and ("negative ion" or ion) and bias and (pulse or pulsed or pulsing) and (RF or "radio frequency")	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:07
13	52	(plasma or "dry etching") same ("negative ion" or ion) same bias same (pulse or pulsed or pulsing) same (RF or "radio frequency")	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:02
14	59	(plasma or "dry etching") same (electron or ion) same bias same (pulse or pulsed or pulsing) same (RF or "radio frequency")	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:05
15	1420	(plasma or "dry etching") and (electron or ion) and bias and (pulse or pulsed or pulsing) and (RF or "radio frequency")	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:04
16	310	((plasma or "dry etching") and (electron or ion) and bias and (pulse or pulsed or pulsing) and (RF or "radio frequency")) and 438/\$.cccls.	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:04
17	258	(plasma or "dry etching") same (electron or ion) same bias same (pulse or pulsed or pulsing)	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:06
18	255	plasma same (electron or ion) same bias same (pulse or pulsed or pulsing)	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:06
19	124	(plasma same (electron or ion) same bias same (pulse or pulsed or pulsing)) and etch\$4	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:06
20	1293	(plasma or "dry etching") and ("negative ion" or "positive ion" or ion) and bias and puls\$3 and (RF or "radio frequency")	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:08
21	271	((plasma or "dry etching") and ("negative ion" or "positive ion" or ion) and bias and puls\$3 and (RF or "radio frequency")) and (chlorine or "Cl.sub.2")	USPAT; EPO; JPO; IBM_TDB	2004/01/14 17:08